

Reg No : Name :

**MAR ATHANASIUS COLLEGE OF ENGINEERING, KOTHAMANGALAM**

(Govt. Aided Autonomous Institution)

Third Semester B.Tech. Degree (SAY) Examination, February, 2026

Course Code: B24EC2T01

Course Name: ANALOG CIRCUITS 2

Max. Marks: 100

Duration:3 Hours

PART - A: 30 Marks (10 Qns x 3 Marks)**Answer all questions**

1. Draw the symbols of enhancement mode n channel and p channel MOSFETs by marking its terminals.
2. Write the expression for threshold voltage including body effect in a MOSFET.
3. Explain how a diode-connected MOSFET can act as an active resistor.
4. Explain why biasing by fixing V_{GS} is not considered a good technique for MOSFETs.
5. Review the effects of the internal capacitors in the frequency response of a CS amplifier.
6. Compare between Common Source amplifier and Common Gate amplifier.
7. State the factors that limit the linear region in the transfer characteristic of a differential amplifier.
8. Define a differential amplifier and mention two of its main applications.
9. Examine the role of biasing in reducing crossover distortion.
10. What are the different types of distortions in a power amplifier?

PART - B: 70 Marks (5 Qns x 14 Marks)**Answer any One full question from each module.****Module 1**

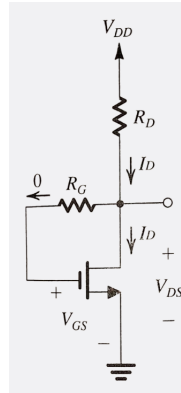
11. a) Examine the key components of the low-frequency small-signal model of an NMOS transistor in the saturation region, and explain their physical significance. (7 marks)
b) Discuss the differences between the low-frequency and high-frequency small-signal models of a MOSFET. (7 marks)

OR

12. a) Derive the expression for drain current in different regions of operation of a MOSFET. (8 marks)
b) An enhancement-type NMOS transistor with $V_t = 0.7V$ has its source terminal grounded and a 1.5V DC applied to the gate. In what region does the device operate for i) $V_D = 0.5V$ ii) $V_D = 0.9V$ iii) $V_D = 3V$ (6 marks)

Module 2

13. a) Explain the working principle of MOSFET biasing with a drain-to-gate feedback resistor. (7 marks)
- b) Design the circuit to operate at a DC drain current of 0.5mA. Assume $V_{DD}=+5V$, $k_n' W/L=1mA/V^2$, $V_t=1V$ and $\lambda=0$. Determine the values of R_D , I_D and V_D . (7 marks)



OR

14. a) A simple N-channel MOSFET current mirror has a reference current of 50 μA , with both transistors having $k' = 100 \mu A/V^2$, $V_t = 0.7 V$, and $W/L = 10$ for the reference transistor. Calculate the output current if the output transistor has $W/L = 20$. (8 marks)
- b) Describe the impact of temperature variations on the performance of a simple MOSFET current mirror. How do changes in mobility and threshold voltage affect the output current? (6 marks)

Module 3

15. Derive the expression for input impedance, output impedance and voltage gain of Common Drain amplifier with active load with suitable diagrams.

OR

16. a) Compare the bandwidth performance of common-source, common-gate, and cascode amplifiers. (7 marks)
- b) Explain the effect of load resistance on the bandwidth of MOSFET amplifiers and how it can be optimized. (7 marks)

Module 4

17. Derive an expression for the Common-Mode Rejection Ratio (CMRR) considering drain resistance mismatch.

OR

18. a) Discuss the trade-off between gain and bandwidth in CS and cascode amplifiers. Examine how cascode offer both high gain and wider bandwidth. (7 marks)
- b) Discuss the effect of finite output resistance and finite tail current source resistance on the small signal gain. (7 marks)

Module 5

19. a) Compare and contrast series-fed and Transformer-Coupled class A amplifiers in terms of power output, efficiency, and signal swing. (7 marks)
- b) What is a class C amplifier? Discuss the limitations of class C amplifiers for use in audio frequency amplification. (7 marks)

OR

20. a) Explain the biasing condition of a Class C amplifier and why it conducts for less than 180° of the input signal. (7 marks)
- b) Describe the method for calculating DC input power, AC output power, and power dissipation in a transformer-coupled amplifier. (7 marks)
